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	Application No.	Applicant(s)	
Notice of Allowability	10/625,277	DONG-SAUK KIM	
	Examiner	Art Unit	
	Thanh Y. Tran	2822	
The MAILING DATE of this communication apper All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in or other appropriate commu IGHTS. This application is s	this application. If not include inication will be mailed in due	ed course. THIS
1. This communication is responsive to <u>5/17/07</u> .			
2. ☑ The allowed claim(s) is/are <u>7-11,13-17 and 19-29</u> .			
3. Acknowledgment is made of a claim for foreign priority una) All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority documents have international Bureau (PCT Rule 17.2(a)). * Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 4. A SUBSTITUTE OATH OR DECLARATION must be subminsFORMAL PATENT APPLICATION (PTO-152) which give 5. CORRECTED DRAWINGS (as "replacement sheets") must (a) including changes required by the Notice of Draftspers 1) hereto or 2) to Paper No./Mail Date (b) including changes required by the attached Examiner's Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR 1. each sheet. Replacement sheet(s) should be labeled as such in the such sheet. Replacement sheet(s) should be labeled as such in the such sheet.	e been received. e been received in Application cuments have been received of this communication to file IENT of this application. eitted. Note the attached EXA es reason(s) why the oath or set be submitted. es on's Patent Drawing Review as Amendment / Comment or 1.84(c)) should be written on the	n No I in this national stage applicate a reply complying with the recommendate and the recommendate and the stage applicate at the recommendate and the stage applicate and the recommendate and the stage application and the stage application are stage application.	juirements OTICE OF
DEPOSIT OF and/or INFORMATION about the depo- attached Examiner's comment regarding REQUIREMENT			lote the
Attachment(s) 1. ☐ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☐ Information Disclosure Statements (PTO/SB/08), Paper No./Mail Date 4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material	6. ☐ Interview Su Paper No./l 7. ☐ Examiner's	formal Patent Application Immary (PTO-413), Mail Date Amendment/Comment Statement of Reasons for Allo	wance

Allowable Subject Matter

1. Claims 7-11, 13-17 and 19-29 are allowed.

2. The following is a statement of reasons for the indication of allowable subject matter:

The prior art of record and to the examiner's knowledge does not teach or render obvious, at least to the skilled artisan, the instant invention regarding a semiconductor device comprises a plurality of capacitor plugs are formed within a predetermined interval interleaved between two bit lines; particularly characterized by comprising a plurality of lower electrodes of capacitors; each lower electrode is octagonally or circularly shaped; and a plurality of contact pads are formed between the lower electrodes and the capacitor plugs, wherein the contact pads are formed over the capacitor plugs and disposed at a lower plane of at least one of the paired lower electrodes, as recited in independent claim 7. Claims 8-11, and 25-29 are dependent upon independent claim 7.

The prior art of record and to the examiner's knowledge does not teach or render obvious, at least to the skilled artisan, the instant invention regarding a method for fabricating a semiconductor device, comprises a plurality of capacitor plugs are formed within a predetermined interval interleaved between two bit lines; particularly characterized by comprising a plurality of lower electrodes of capacitors, each lower electrode is octagonally or circularly shaped; depositing a sacrifice insulation layer over the capacitor plug formed over a semiconductor substrate, forming a plurality of open parts exposing the capacitor plugs by performing an selective etching of the sacrifice insulation layer by using a mask pattern; depositing a material for the lower electrode on an entire profile of the semiconductor substrate comprising the open parts; forming the lower electrodes separated from each other by

performing a planerization process until the sacrifice insulation layer is exposed; and removing the sacrifice insulation layer by carrying out a wet dip-out process, as recited in independent claim 13. Claims 14-17 are dependent upon independent claim 13.

The prior art of record and to the examiner's knowledge does not teach or render obvious, at least to the skilled artisan, the instant invention regarding a method for fabricating a semiconductor device, comprises a plurality of capacitor plugs are formed within a predetermined interval interleaved between two bit lines; particularly characterized by comprising a plurality of lower electrodes of capacitors, each lower electrode is octagonally or circularly shaped; a plurality of contact pads are respectively formed between the lower electrodes and the capacitor plugs after forming the capacitor plugs, wherein the contact pads serve as connecting the lower electrode with the capacitor plug electrically, in independent claim 19. Claims 20-24 are dependent upon independent claim 19.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Contact Information

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thanh Y. Tran whose telephone number is (571) 272-2110. The examiner can normally be reached on M-F (9-6:30pm):

Application/Control Number: 10/625,277 Page 4

Art Unit: 2822

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Zandra Smith can be reached on (571) 272-2429. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

TYT

Zandra V. Smith
Zandra V. Smith
Supervisory Patent Examiner